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ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3

EcoSPARK® 300mJ, 400V, N-Channel Ignition IGBT

General Description

The ISL9V3040D3S, ISL9V3040S3S, ISL9V3040P3, and ISL9V3040S3 are the next generation ignition IGBTs that offer outstanding SCIS capability in the space saving D-Pak (TO-252), as well as the industry standard D²-Pak (TO-263), and TO-262 and TO-220 plastic packages. This device is intended for use in automotive ignition circuits, specifically as a coil driver. Internal diodes provide voltage clamping without the need for external components.

EcoSPARK® devices can be custom made to specific clamp voltages. Contact your nearest Fairchild sales office for more information.

Formerly Developmental Type 49362

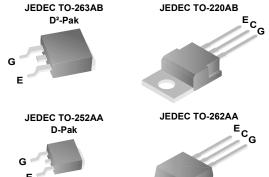
Applications

- · Automotive Ignition Coil Driver Circuits
- · Coil- On Plug Applications

Features

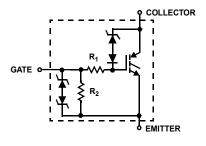
- · Space saving D-Pak package availability
- SCIS Energy = 300mJ at T_{.I} = 25°C
- · Logic Level Gate Drive

Package



COLLECTOR (FLANGE)

Symbol



Device Maximum Ratings T_A = 25°C unless otherwise noted

Symbol	Parameter	Ratings	Units	
BV _{CER}	Collector to Emitter Breakdown Voltage (I _C = 1 mA)	430	V	
BV _{ECS}	Emitter to Collector Voltage - Reverse Battery Condition (I _C = 10 mA)	24	V	
E _{SCIS25}	At Starting T _J = 25°C, I _{SCIS} = 14.2A, L = 3.0 mHy	300	mJ	
E _{SCIS150}	At Starting T _J = 150°C, I _{SCIS} = 10.6A, L = 3.0 mHy	170	mJ	
I _{C25}	Collector Current Continuous, At T _C = 25°C, See Fig 9	21	Α	
I _{C110}	Collector Current Continuous, At T _C = 110°C, See Fig 9	17	Α	
V_{GEM}	Gate to Emitter Voltage Continuous	±10	V	
P_{D}	Power Dissipation Total T _C = 25°C	150	W	
	Power Dissipation Derating T _C > 25°C	1.0	W/°C	
T _J	Operating Junction Temperature Range	-40 to 175	°C	
T _{STG}	Storage Junction Temperature Range	-40 to 175	°C	
TL	Max Lead Temp for Soldering (Leads at 1.6mm from Case for 10s)	300	°C	
T _{pkg}	Max Lead Temp for Soldering (Package Body for 10s)	260	°C	
ESD	Electrostatic Discharge Voltage at 100pF, 1500Ω	4	kV	

Device M	larking	Device	Р	ackage	Reel Size	Тар	e Width	Qua	antity
V3040D		ISL9V3040D3ST	TC)-252AA	330mm	16mm		2500	
V3040S ISL9V3040S3ST			TO-263AB		330mm	24mm		800	
V3040P ISL9V3040P3 T0			TC	D-220AB Tube		N/A		50	
V3040S ISL9V3040S3 TO			TC	D-262AA Tube		N/A		50	
V304	0D	ISL9V3040D3S	TO-252AA		Tube	N/A		75	
V3040S ISL9V3040S3S TO)-263AB	Tube	N/A		50		
lectrica	al Chai	acteristics T _A = 25	°C unl	ess otherwise r	noted				
Symbol	1	Parameter		Test Cor		Min	Тур	Max	Unit
ff State	Charact			1031 001	iditions		136	Max	0
			tono	L = 2m / \/	- 0	270	400	420	V
BV _{CER}	Collector to Emitter Breakdown Voltage			$I_C = 2mA$, V_{GE}		370	400	430	V
				R_G = 1KΩ, See Fig. 15 T_J = -40 to 150°C					
BV _{CES}	Collector	to Emitter Breakdown Vol	tage	$I_C = 10 \text{mA}, V_G$		390	420	450	V
020				$R_G = 0$, See F	ig. 15				
				$T_J = -40 \text{ to } 150$					
BV_{ECS}	Emitter to	Collector Breakdown Vol	tage	$I_C = -75 \text{mA}, V_C$	_{SE} = 0V,	30	-	-	V
D) /	0-4-4-5				T _C = 25°C				V
BV _{GES}		Emitter Breakdown Voltage		$I_{GES} = \pm 2mA$	T - 25°C	±12	±14	- 25	
ICER	Collector	to Emitter Leakage Curre	nt	$V_{CER} = 250V$, $R_G = 1K\Omega$,	$T_C = 25^{\circ}C$ $T_C = 150^{\circ}C$	-	-	25	μA
				See Fig. 11	1 _C = 150 C	-	-	1	mA
I _{ECS}	Emitter to	Collector Leakage Curre	nt	V _{FC} = 24V, See	e T _C = 25°C	-	-	1	m/
.509		J		Fig. 11	T _C = 150°C	-	-	40	m/
R ₁	Series G	ate Resistance		10	-	70	-	Ω	
R ₂	Gate to E	Emitter Resistance			10K	-	26K	Ω	
n State (Charact	eristics			l.		l.		
		to Emitter Saturation Volta	200	I _C = 6A,	T _C = 25°C,	_	1.25	1.60	V
V _{CE(SAT)}	Collector	to Emitter Saturation voite	age	V _{GE} = 4V	See Fig. 3	-	1.25	1.00	· ·
V _{CE(SAT)}	Collector	to Emitter Saturation Volta	age	I _C = 10A,	T _C = 150°C,	_	1.58	1.80	V
CE(SAI)			-3-	V _{GE} = 4.5V	See Fig. 4				-
V _{CE(SAT)}	Collector	Collector to Emitter Saturation Voltage			T _C = 150°C	-	1.90	2.20	V
- (- /				V _{GE} = 4.5V					
ynamic	Charact	eristics							
$Q_{G(ON)}$	Gate Ch			I _C = 10A, V _{CE}	= 12V.	_	17	_	nC
		95		$V_{GE} = 5V$, See					
$V_{GE(TH)}$	Gate to I	Emitter Threshold Voltage		I _C = 1.0mA,	T _C = 25°C	1.3	-	2.2	V
				$V_{CE} = V_{GE}$	T _C = 150°C	0.75	-	1.8	V
				See Fig. 10	1.5				ļ
V_{GEP}	Gate to I	Emitter Plateau Voltage		I _C = 10A, V _{CE}	= 12V	-	3.0	-	V
witching	, Charac	teristics							
t _{d(ON)R}	Current 7	Turn-On Delay Time-Resis	tive	$V_{CE} = 14V, R_{L} = 1\Omega,$		-	0.7	4	μs
	Current Rise Time-Resistive			$V_{GE} = 5V, R_G = 1K\Omega$		-	2.1	7	μs
t _{rR}				T _J = 25°C, See Fig. 12			1	ļ	
	Current	Turn-Off Delay Time-Induct	tive	$V_{CE} = 300V, L$			4.8	15	μs
t _{d(OFF)L}	_			V_{GE} = 5V, R _G = 1KΩ T _J = 25°C, See Fig. 12		-	2.8	15	μs
	_	Fall Time-Inductive		1 = /5 (544					1
t _{d(OFF)L}	Current I					_	_	300	m.
t _{d(OFF)L}	Current I	Fall Time-Inductive		T _J = 25°C, L =	3.0 mHy,	-	-	300	m
t _{d(OFF)L}	Current I				3.0 mHy,	-	-	300	m

Typical Performance Curves

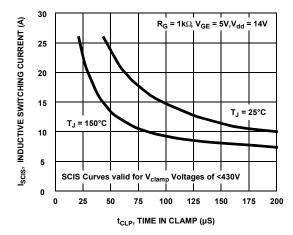


Figure 1. Self Clamped Inductive Switching Current vs Time in Clamp

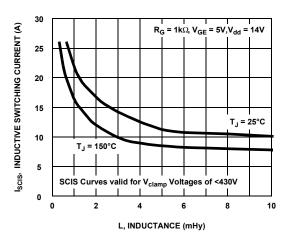


Figure 2. Self Clamped Inductive Switching Current vs Inductance

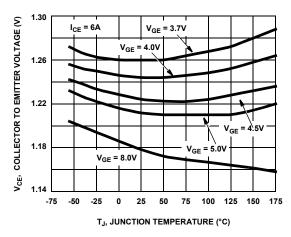


Figure 3. Collector to Emitter On-State Voltage vs Junction Temperature

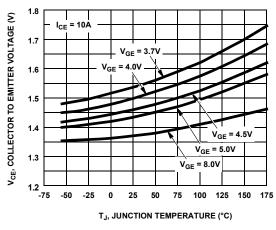


Figure 4. Collector to Emitter On-State Voltage vs Junction Temperature

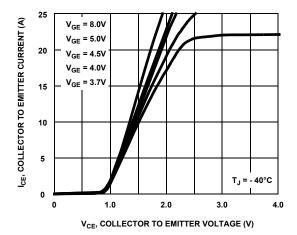


Figure 5. Collector to Emitter On-State Voltage vs Collector Current

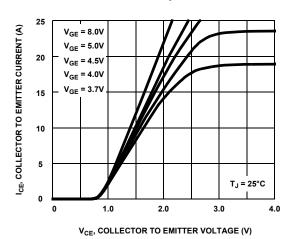


Figure 6. Collector to Emitter On-State Voltage vs Collector Current

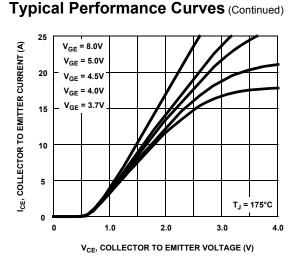


Figure 7. Collector to Emitter On-State Voltage vs Collector Current

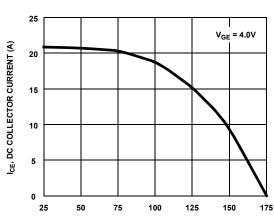


Figure 9. DC Collector Current vs Case Temperature

T_C, CASE TEMPERATURE (°C)

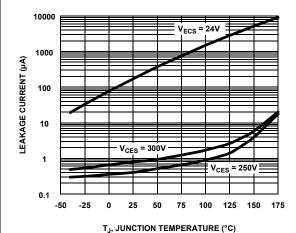


Figure 11. Leakage Current vs Junction Temperature

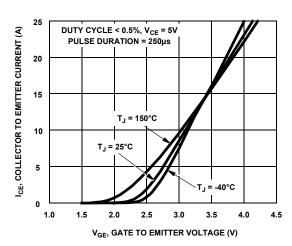


Figure 8. Transfer Characteristics

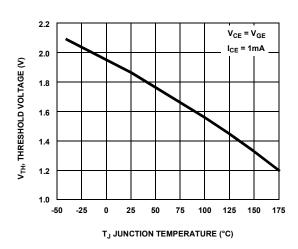


Figure 10. Threshold Voltage vs Junction Temperature

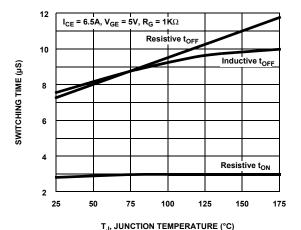
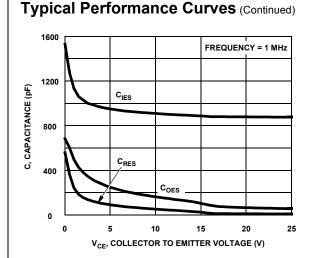


Figure 12. Switching Time vs Junction Temperature



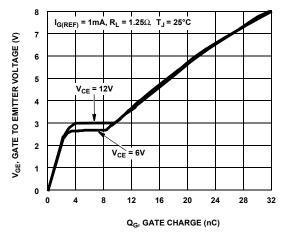


Figure 13. Capacitance vs Collector to Emitter Voltage

Figure 14. Gate Charge

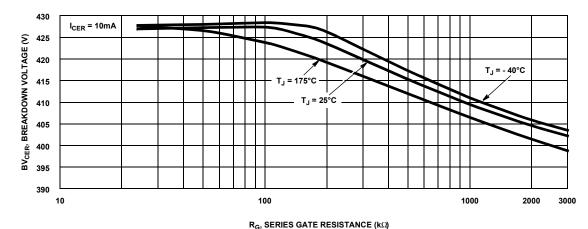


Figure 15. Breakdown Voltage vs Series Gate Resistance

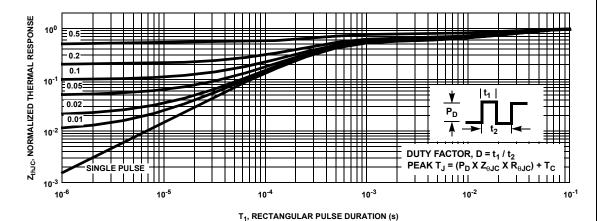
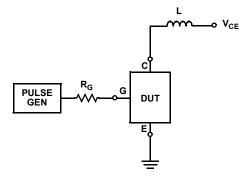


Figure 16. IGBT Normalized Transient Thermal Impedance, Junction to Case

Test Circuit and Waveforms



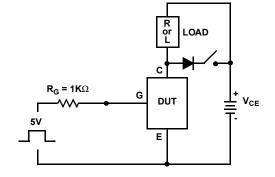


Figure 17. Inductive Switching Test Circuit

Figure 18. t_{ON} and t_{OFF} Switching Test Circuit

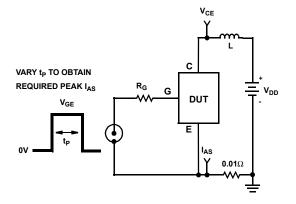


Figure 19. Energy Test Circuit

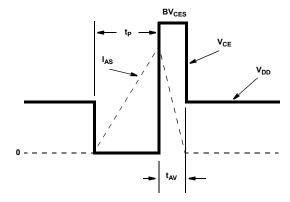


Figure 20. Energy Waveforms

SPICE Thermal Model REV 7 March 2002 JUNCTION ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3 CTHERM1 th 6 2.1e -3 CTHERM2 6 5 1.4e -1 CTHERM3 5 4 7.3e -3 CTHERM4 4 3 2.1e -1 RTHERM1 CTHERM1 CTHERM5 3 2 1.1e -1 CTHERM6 2 tl 6.2e +6 RTHERM1 th 6 1.2e -1 6 RTHERM2 6 5 1.9e -1 RTHERM3 5 4 2.2e -1 RTHERM4 4 3 6.0e -2 RTHERM2 CTHERM2 RTHERM5 3 2 5.8e -2 RTHERM6 2 tl 1.6e -3 SABER Thermal Model 5 SABER thermal model ISL9V3040D3S / ISL9V3040S3S / ISL9V3040P3 / ISL9V3040S3 RTHERM3 CTHERM3 template thermal_model th tl thermal_c th, tl 4 ctherm.ctherm1 th 6 = 2.1e - 3ctherm.ctherm2 6 5 = 1.4e -1 ctherm.ctherm3 5 4 = 7.3e -3 ctherm.ctherm4 4 3 = 2.2e -1 RTHERM4 CTHERM4 ctherm.ctherm5 3 2 =1.1e -1 ctherm.ctherm6 2 tl = 6.2e +6 rtherm.rtherm1 th 6 = 1.2e -1 3 rtherm.rtherm2 6 5 = 1.9e - 1rtherm.rtherm3 5 4 = 2.2e -1 rtherm.rtherm4 4 3 = 6.0e -2 RTHERM5 CTHERM5 rtherm.rtherm5 3 2 = 5.8e -2 rtherm.rtherm6 2 tl = 1.6e -3 2 RTHERM6 CTHERM6

CASE

tl





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Definition of Torms

Definition of Terms						
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Preliminary	First Production	Datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.				
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